

AMENDMENTS TO THE CLAIMS

The listing of claims below replaces all prior versions of claims in the application.

1. (Currently amended) A semiconductor device comprising:
 - a first insulating film formed over a semiconductor substrate;
 - a gate electrode formed over the semiconductor substrate;
 - an interconnection buried in at least a surface side of the first insulating film and formed horizontally with respect to the semiconductor substrate, the interconnection having a main interconnection portion extended perpendicularly to an extending direction of the gate electrode and being in contact with the gate electrode and an extended portion provided at an end part of the main interconnection portion and extended perpendicularly horizontally with respect to [[an]] the extending direction of the gate electrode ~~main interconnection portion, a width of the extended portion in the extending direction of the main interconnection portion being below a width of the main interconnection portion;~~ and
 - a second insulating film formed on the first insulating film and having a contact hole down to the end part of the main interconnection portion of the interconnection.
2. (Original) A semiconductor device according to claim 1, wherein the extended portion is extended from the end part in one direction perpendicular to the extending direction of the main interconnection portion.

3. (Original) A semiconductor device according to claim 1, wherein the extended portion is extended from the end part in both directions perpendicular to the extending direction of the main interconnection portion.

4. (Canceled)

5. (Original) A semiconductor device according to claim 1, wherein a minimum width of the contact hole is larger than a minimum width of the interconnection.

6. (Currently amended) A semiconductor device comprising:
a first interconnection gate electrode formed over a semiconductor substrate, extended in a first direction;
a first insulating film formed over the semiconductor substrate with the first interconnection gate electrode formed on;
a second an interconnection buried in at least a surface side of the first insulating film and formed horizontally with respect to the semiconductor substrate, the second interconnection having a main interconnection portion extended in a second direction intersecting the first direction, being in contact with the gate electrode and bridging the first interconnection gate electrode and an extended portion provided at an end part of the main interconnection portion

and extended in the first direction, ~~a width of the extended portion in the second direction being below a width of the main interconnection portion;~~ and

 a second insulating film formed on the first insulating film, and having a contact hole down to the end part of the main interconnection portion of the ~~second~~ interconnection.

7-16 (Cancelled).

17. (New) A semiconductor device according to claim 1, wherein a width of the extended portion in the extending direction of the main interconnection portion is below a width of the main interconnection portion.

18. (New) A semi conductor according to claim 6, wherein a width of the extended portion in the second direction is below a width of the main interconnection portion.

19. (New) A semiconductor device comprising:
 a first insulating film formed over a semiconductor substrate;
 a gate electrode formed over the semiconductor substrate;
 an interconnection buried in at least a surface side of the first insulating film and formed horizontally with respect to the semiconductor substrate, the interconnection having a main interconnection portion being in contact with the gate electrode and having a length along an extending direction of the gate electrode larger than a width of the gate electrode and an

Application No. 10/743,438
Attorney Docket No. 032180

Amendment under 37 C.F.R. §1.111
Amendment filed: January 17, 2006

extended portion provided at an end part of the main interconnection portion and extended horizontally with respect to the extending direction of the gate electrode; and
a second insulating film formed on the first insulating film and having a contact hole down to the end part of the main interconnection portion of the interconnection.